

99-0219

The invention relates to the silverless semi-conductive photography.

The carrier consists of the dielectric support with subsequently situated thereon first electrode, photoinjective layer of P-type conductivity, chalcogenide vitreous semiconductor layer and the second electrode in which the photoinjection layer is made of ten interchangeable semi-layer pairs, the lower one is manufactured of As_2Se_3 with a thickness of 8—10 nm and the upper one - of In_2S_3 with a thickness of 10-12 nm or In_2Se_3 with a thickness of 40-50 nm, the registration layer having a thickness of 0,2-0,5 μm , and the second electrode is manufactured of aluminium and has a thickness of 10-50 nm.

The result consists in increasing the light sensibility of the information carrier.